

# ST2001HI

# HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

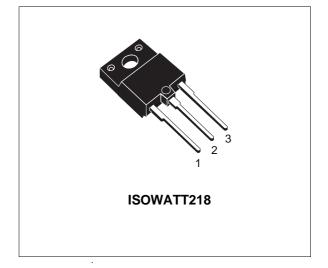
- NEW SERIES, ENHANCED PERFORMANCE
- FULLY INSULATED PACKAGE (U.L. COMPLIANT) FOR EASY MOUNTING
- HIGH VOLTAGE CAPABILITY
- HIGH SWITCHING SPEED
- TIGTHER hfe CONTROL
- IMPROVED RUGGEDNESS

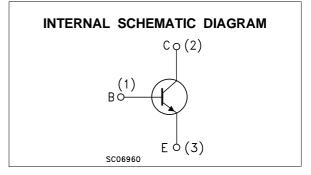
#### **APPLICATIONS:**

 HORIZONTAL DEFLECTION FOR COLOR TVS OVER 21 INCHES AND 15 INCHES MONITORS

#### DESCRIPTION

The ST2001HI is manufactured using Diffused Collector technology for more stable operation Vs base drive circuit variations resulting in very low worst case dissipation.





#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit	
Vсво	Collector-Base Voltage (I <sub>E</sub> = 0)	1500	V	
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	600	V	
V <sub>EBO</sub>	Emitter-Base Voltage $(I_C = 0)$	7	V	
Ιc	Collector Current	10	A	
Ісм	Collector Peak Current (t <sub>p</sub> < 5 ms)	20	A	
IB	Base Current	7	A	
Ptot	Total Dissipation at T <sub>c</sub> = 25 °C	55	W	
V <sub>isol</sub>	Insulation Withstand Voltage (RMS) from All Three Leads to External Heatsink	2500	V	
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C	
Tj	Max. Operating Junction Temperature	150	°C	

#### THERMAL DATA

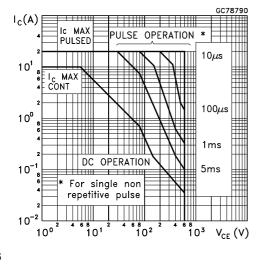
R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	2.3	°C/W	
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## **ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25 \,^{\circ}C$ unless otherwise specified)

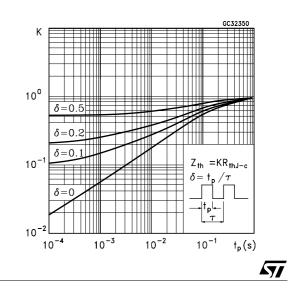
Symbol	Parameter	Test	Conditions	Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = 1500 V V <sub>CE</sub> = 1500 V	T <sub>C</sub> = 125 <sup>o</sup> C			1 2	mA mA
I <sub>EBO</sub>	Emitter Cut-off Current $(I_C = 0)$	V <sub>EB</sub> = 7 V				1	mA
$V_{CEO(sus)^*}$	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 100 mA	L = 25 mH	600			V
V <sub>CE(sat)</sub> *	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5 A	I <sub>B</sub> = 1.25 A			1.5	V
V <sub>BE(sat)</sub> *	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5 A	I <sub>B</sub> = 1.25 A			1.2	V
h <sub>FE</sub> *	DC Current Gain	-	V <sub>CE</sub> = 1 V V <sub>CE</sub> = 5 V	5	4.5	9	
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time	$\label{eq:lc} \begin{array}{l} I_C = 5 \ \text{A} \\ I_{BB(off)} = 2 \ \mu\text{H} \\ f_h = 64 \ \text{KHz} \end{array}$	$I_{Bon(END)} = 850 \text{ mA}$ $V_{BB(off)} = -2.5 \text{ V}$		2.6 0.2	3 0.4	μs μs

\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

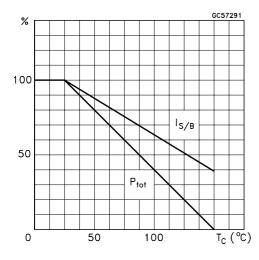
#### Safe Operating Area



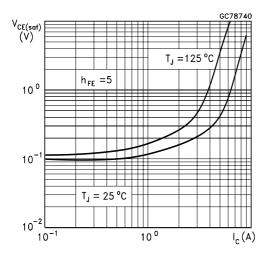
Thermal Impedance



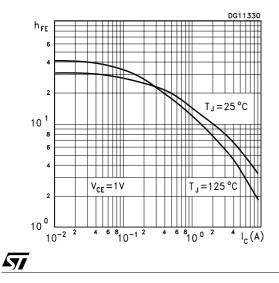
#### **Derating Curve**



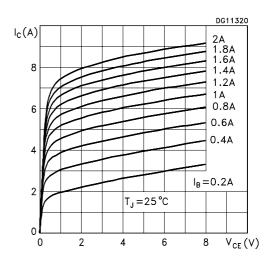
Collector Emitter Saturation Voltage



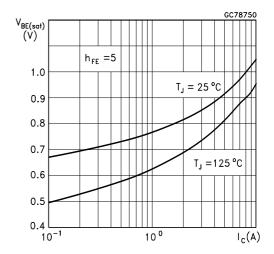
#### DC Current Gain

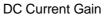


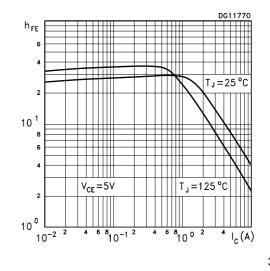
#### **Output Characteristics**



#### Base Emitter Saturation Voltage

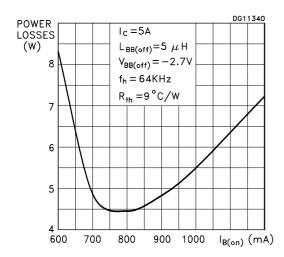






#### ST2001HI

#### Power Losses



RBSOA

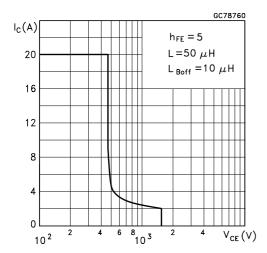
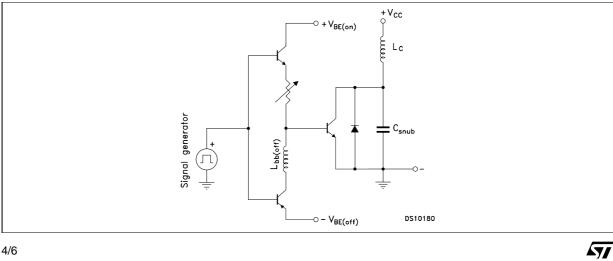
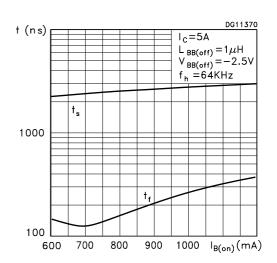


Figure 1: Inductive Load Switching Test Circuit.



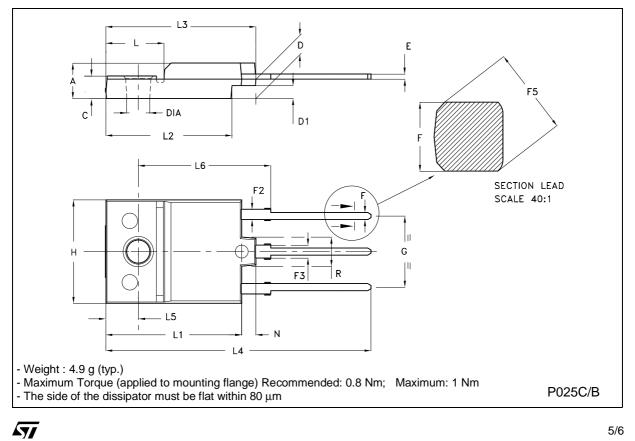
Switching Time Inductive Load



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DIM.	mm		inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	5.35		5.65	0.211		0.222
С	3.30		3.80	0.130		0.150
D	2.90		3.10	0.114		0.122
D1	1.88		2.08	0.074		0.082
E	0.75		0.95	0.030		0.037
F	0.75		0.95	0.030		0.037
F2	1.50		1.70	0.059		0.067
F3	1.90		2.10	0.075		0.083
F5			1.10			0.043
G	10.80		11.20	0.425		0.441
Н	15.80		16.20	0.622		0.638
L		9			0.354	
L1	20.80		21.20	0.819		0.835
L2	19.10		19.90	0.752		0.783
L3	22.80		23.60	0.898		0.929
L4	40.50		42.50	1.594		1.673
L5	4.85		5.25	0.191		0.207
L6	20.25		20.75	0.797		0.817
Ν	2.1		2.3	0.083		0.091
R		4.6			0.181	
DIA	3.5		3.7	0.138		0.146

## **ISOWATT218 NARROW LEADS MECHANICAL DATA**



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